Listing of Claims:

This listing of claims reflects all claim amendments and replaces all prior versions, and listings, of claims in the application (material to be inserted is in **bold and underline**, and material to be deleted is in **strikeout** or (if the deletion is of five or fewer consecutive characters or would be difficult to see) in double brackets [[]].

- 1. (Canceled)
- 2. (Previously Presented) A dielectric thin film prepared by polymerizing an ethylenic-containing precursor with a benzocyclobutane-containing precursor, wherein the ethylenic-containing precursor has a general structure of:

$$P-(-Z-W)_{n^o}$$
 (Ia);

wherein, W is hydrogen, fluorine or a fluorinated phenyl;

P is an aromatic-moiety with a general structure of $-C_6H_{4-n}F_{n-}$ (n = 0 to 4); $-C_6H_{4-n}F_{n-}$ (n = 0 to 4); $-C_{10}H_{6-n}F_{n-}$ (n = 0 to 6), or $-C_{12}H_{8-n}F_{n-}$ (n = 0 to 8);

Z is a moiety having an ethylenic group; and n° is an integer of 2.

3. (Previously Presented) The dielectric thin film of claim 2, wherein the benzyocyclobutane containing precursor has a general structure of:

$$P' \left(\begin{array}{c} W''''' \\ W''''' \end{array} \right) W'''$$

$$W''''' W''''$$

$$M''''' W''''$$

$$M''''' W''''$$

$$M''''' W''''$$

wherein W', W", W"", W"", and W""" are independently the same or different and are hydrogen, fluorine or a fluorinated phenyl;

P' is an aromatic-moiety with a general structure of $-C_6H_{4-n}F_{n^-}$ (n = 0 to 4); $-C_6H_{4-n}F_{n^-}CF_2-C_6H_{4-n}F_{n^-}$ (n = 0 to 4); $-C_{10}H_{6-n}F_{n^-}$ (n = 0 to 6), or $-C_{12}H_{8-n}F_{n^-}$ (n = 0 to 8); and

n' is an integer of 2.

- 4. (Original) The dielectric thin film of claim 2, wherein the dielectric thin film has a dielectric constant (" ϵ ") value equal to or less than 2.6.
- 5. (Original) The dielectric thin film of claim 2, wherein one or more layers of the thin film is deposited inside an integrated circuit ("IC") or an electronic device.
- 6. (Original) The dielectric thin film of claim 5, wherein the electronic device comprises an active matrix liquid crystal display, or a fiber optic device.
- 7. (Original) The dielectric thin film of claim 5, wherein the IC is manufactured via a dual damascene process comprising the dielectric thin film.
 - 8. (Canceled)
 - 9. (Canceled)

- 10. (Canceled)
- 11. (Canceled)
- 12. (Canceled)
- 13. (Canceled)
- 14. (Canceled)
- 15. (Canceled)
- 16. (Canceled)
- 17. (Canceled)
- 18. (Canceled)
- 19. (Canceled)
- 20. (Canceled)
- 21. (Canceled)
- 22. (Canceled)
- 23. (Canceled)
- 24. (Canceled)
- 25. (Canceled)
- 26. (Canceled)